

PAPERS FROM THE 19TH WOKSHOP ON DIELECTRICS IN MICROELECTRONICS (WODIM 2016)

F

Effects of interface states and near interface traps on the threshold voltage stability of GaN and SiC transistors employing SiO₂ as gate dielectric

Patrick Fiorenza, Giuseppe Greco, Filippo Giannazzo, Ferdinando Iucolano and Fabrizio Roccaforte
J. Vac. Sci. Technol. B **35**, 01A101 (2017);
<http://dx.doi.org/10.1116/1.4967306>

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F

High-k/GaN interface engineering toward AlGaN/GaN MIS-HEMT with improved V_{th} stability

Nadine Szabó, Andre Wachowiak, Annett Winzer, Johannes Ocker, Jan Gärtner, Rico Hentschel, Alexander Schmid and Thomas Mikolajick
J. Vac. Sci. Technol. B **35**, 01A102 (2017);
<http://dx.doi.org/10.1116/1.4967307>

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Impact of temperature on conduction mechanisms and switching parameters in HfO₂-based 1T-1R resistive random access memories devices

Eduardo Pérez, Christian Wenger, Alessandro Grossi, Cristian Zambelli, Piero Olivo and Robin Roelofs
J. Vac. Sci. Technol. B **35**, 01A103 (2017);
<http://dx.doi.org/10.1116/1.4967308>

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